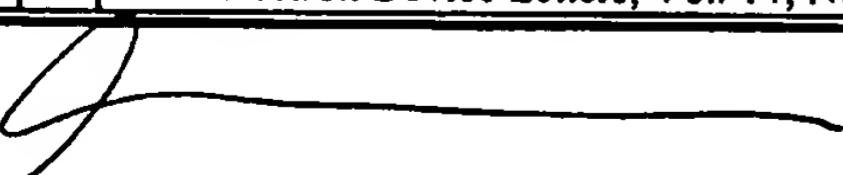
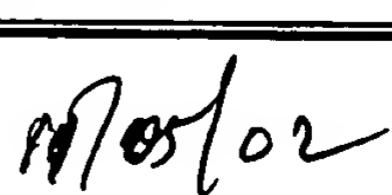


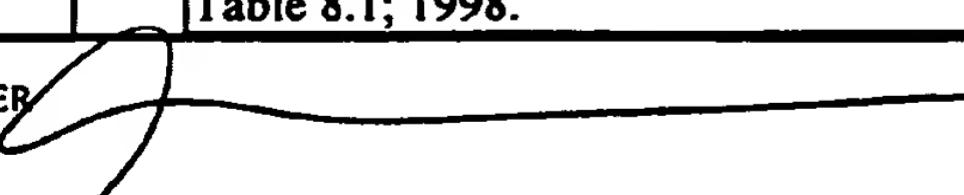
FORM PTO-1449 (Modified)  LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT		ATTY. DOCKET NO. YOR919990123US2	SERIAL NO.: 09/936,320
			
(Use several sheets if necessary)		APPLICANT: Jack O. Chu	
		FILING DATE: September 12, 2001	GROUP: 2811

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS					
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
✓	AA	5,019,882	05/28/1991	Solomon et al.	357	23.8	May 15, 1989
✓	AB	5,534,713	07/09/1996	Ismail et al.	257	24	May 20, 1994
✓	AC	5,241,197	08/31/1993	Murakami et al.	257	192	September 13, 1991
✓	AD	5,298,452	03/29/1994	Meyerson	437	81	February 21, 1992
✓	AE	5,659,187	08/19/1997	Legoues et al.	257	190	June 7, 1995
✓	AF	5,241,197	08/31/1993	Murakami et al.	257	192	September 13, 1991
✓	AG	5,259,918	11/09/1993	Akbar et al.	156	610	June 12, 1991
	AH						

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES
✓	AJ	05 121450 A	15/05/1993	Japan	H01L	21/338	NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
✓	AM	R. People and J.C. Bean, "Band Alignments Of Coherently Strained Ge <sub>x</sub> Si <sub>1-x</sub> / Si Heterostructures On <001> Ge <sub>x</sub> Si <sub>1-x</sub> Substrates"; Appl. Phys. Lett. 48 (8); pp. 538-539; February 24, 1986.					
✓	AN	G. Hock et al., "High Performance 0.25μm p-Type Ge/SiGe MODFETs"; Electronics Letters; Vol. 34; No. 19; pp. 1888-1889; September 17, 1998.					
✓	AO	U. Konig and F. Schaffler, "p-Type Ge-Channel MODFET's With High Transconductance Grown On Si Substrates"; IEEE Electron Device Letters; Vol. 14; No. 4; pp. 205-207; April 1993.					

EXAMINER 	DATE CONSIDERED 
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)			ATTY. DOCKET NO. YOR919990123US2		SERIAL NO.: 09/936,320		
			APPLICANT: Jack O. Chu				
			FILING DATE: September 12, 2001		GROUP: 2811		
REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS				
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
	BA						
	BB						
	BC						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES
	BD						NO
	BE						
	BF						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>h</i>	BE	M. Arafa, "A 70-GHz $f_T$ Low Operating Bias Self-Aligned p-Type SiGe MODFET"; IEEE Electron Device Letters; Vol. 17; No. 12; pp. 586-588; December 1996.					
<i>g</i>	BF	U. Kong et al., "SiGe HBTs And HFETs"; IEEE Solid State Electronics; Vol. 38; No. 9; pp. 1595-1602; Elsevier; 1995.					
<i>g</i>	BG	Milind Gokhale et al., "Enhanced Performance Of PMOS and CMOS Circuits Using Self-Aligned MOSFETs With Modulation Doped Si-Ge Channel"; Proceedings of the Tenth Biennial University/ Government/Industry Microelectronics Symposium; 1993 IEEE; US; New York; pp.219-222; May 18-19, 1993.					
<i>g</i>	BH	David W. Greve, "Field Effect Devices And Applications"; Prentice-Hall, Inc; Simon & Schuster/ A Viacom Company; Upper Saddle River, NJ, 07458; Chap. 8: Structure Of The GaAs MESFET; p.315; Table 8.1; 1998.					
EXAMINER 				DATE CONSIDERED <i>11/05/02</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							